The Ge-In-Ni (Germanium-Indium-Nickel) System

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Introduction

Very little work has been done in the Ge-In-Ni system. Only one isothermal section has been established and is reported here.

Binary Systems

The Ge-In system [Massalski2] (Fig. 1) is a simple eutectic system with the eutectic point very close to In. The eutectic temperature is 156.29 °C. There is practically no solubility of In in Ge, nor of Ge in In.

The Ge-Ni system [1991Nas] (Fig. 2) has nine intermediate phases: β GeNi₃ (β), γ_1 GeNi₃ (γ_1), δ Ge₂Ni₅ (δ), GeNi₂ (π), ϵ 'Ge₃Ni₅ (ϵ '), ϵ Ge₃Ni₅ (ϵ), Ge₁₂Ni₁₉ (ζ), Ge₂Ni₃ (ξ), and GeNi (ι). The β and ϵ phases melt congruently at 1132 and 1185 °C, respectively and the $\epsilon \rightarrow \epsilon'$ transformation occurs congruently at ~398 °C. The γ_1 , δ , ζ , ξ , and ι phases form through peritectic reactions: L + $\beta \leftrightarrow \gamma$ at 1118 °C, L + $\gamma_1 \leftrightarrow \delta$ at 1102 °C, L + $\epsilon \leftrightarrow \zeta$ at 1050 °C, L + $\zeta \leftrightarrow \xi$ at 990 °C, and L + $\xi \leftrightarrow \iota$ at 850 °C. The π phase forms through a peritectoid reaction $\beta + \varepsilon \leftrightarrow \pi$ at 506 °C. Three eutectic reactions $L \leftrightarrow \gamma + \beta$, $L \leftrightarrow \delta + \varepsilon$, and $L \leftrightarrow \iota + (Ge)$ occur at 1124, 1099, and 762 °C, respectively. γ is the terminal face-centered cubic (fcc) solid solution (Ni). The γ_1 and δ phases exist only at high temperatures and undergo eutectoid transformation $\gamma_1 \leftrightarrow \beta + \delta$ and $\delta \leftrightarrow \beta + \varepsilon$ at 1082 and 1045 °C, respectively. The ζ , ξ , and ε phases undergo four eutectoid transformations: $\xi \leftrightarrow \zeta + \iota$, $\varepsilon \leftrightarrow \varepsilon' + \zeta$, $\zeta \leftrightarrow \varepsilon' + \iota$, and $\varepsilon \leftrightarrow \pi + \varepsilon'$ at 515, ~394, 382, and 290 °C, respectively.

The In-Ni system [1991Nas] (Fig. 3) has eight intermediate phase: InNi₃ (τ), InNi₂ (λ), In₉Ni₁₆ (ϵ), In₉Ni₁₃ (ρ), InNi (θ), InNi (δ_1), In₃Ni₂ (ν), and In₇₂Ni₂₈ (η), of which the ϵ and δ phases melt congruently at 990 and 950 °C, respectively. The ν and η phases form through peritectic reactions L + $\delta \leftrightarrow \nu$ at 870 °C and L + $\nu \leftrightarrow \eta$ at 409 °C. The τ , λ , ρ , and θ phases form through peritectid reactions γ + ϵ $\leftrightarrow \tau$, $\tau + \epsilon \leftrightarrow \lambda$, $\epsilon + \delta_1 \leftrightarrow \rho$, and $\rho + \delta_1 \leftrightarrow \theta$ at 848, 665, 876, and 860 °C, respectively. The ϵ and δ phases undergo eutectoid transformation $\epsilon \leftrightarrow \lambda + \rho$ at 482 °C and $\delta_1 \leftrightarrow$ $\theta + \nu$ at 770 °C. Three eutectic reactions L $\leftrightarrow \gamma + \epsilon$, L \leftrightarrow $\epsilon + \delta$, and L + η + (In) occur at 910, 918, and ~156 °C, respectively. The Ni₂In phase has an invariant composition.



Fig. 1 Binary Ge-In phase diagram [Massalski2]



Fig. 2 Binary Ge-Ni phase diagram [1991Nas]



Fig. 3 Binary In-Ni phase diagram [1991Nas]

Binary and Ternary Phases

In the three binary systems Ge-In, Ge-Ni, and In-Ni, 17 intermediate phases form. No ternary intermediate phase has been reported in the Ge-In-Ni system. The binary phases and their structure data are given in Table 1.

Ternary System

The Ge-In-Ni system has been investigated by [1982Bor]. The alloys were melted, using pure metals of 99.9 mass% purity, in evacuated and sealed quartz tubes, homogenized at 800 °C, then annealed at 650 °C for 12 h and water

Phase designation	Composition (a)	Pearson's symbol	Space group	Туре	Lattice parameter, nm		
					а	b	с
γ	(Ni)	cF4	$Fm\overline{3}m$	Cu			
In	(In)	tI2	I4/mmm	In			
Ge	(Ge)	cF8	$Fd\overline{3}m$	C (diamond)			
β	βGeNi ₃	cP4	$Pm\overline{3}m$	AuCu ₃	0.357		
γ1	γ ₁ GeNi ₃						
δ	δGe ₂ Ni ₅	hP84	$P6_3/mmc$	Pd_5Sb_2	0.6827		1.2395
π	GeNi ₂	oP12	Pnma	Co ₂ Si	0.7264	0.511	0.383
ε′	ε'Ge ₃ Ni ₅	mC32	<i>C</i> 2	Ge ₃ Ni ₅	1.1682	0.6737	0.6364
					$\beta = 52.1^{\circ}$		
3	εGe ₃ Ni ₅	hP4	$P6_3/mmc$	AsNi	0.3955		0.5047
ζ	Ge ₁₂ Ni ₁₉	mC62	<i>C</i> 2	Ge ₁₂ Ni ₁₉	1.1631	0.6715	1.0048
						$\beta = 90^{\circ}$	
٤	Ge ₂ Ni ₃	hP4	$P6_3/mmc$	AsNi	0.386		0.500
1 I	GeNi	oP8	Pnma	MnP	0.581	0.538	0.343
τ	InNi ₃	hP8	$P6_3/mmc$	Ni ₃ Sn	0.5320		0.4242
λ	InNi ₂	hP6	$P6_3/mmc$	InNi ₂	0.4179		0.5131
3	In ₉ Ni ₁₆ (31.0-41.5)	hP4	$P6_3/mmc$	AsNi	0.41889		0.51230
ρ	In ₉ Ni ₁₃ (38.5-42.2)						
θ	InNi	hP6	P6/mmm	CoSn	0.4537		0.4345
δ_1	InNi	cP2	$Pm\overline{3}m$	CsCl	0.3093		
ν	In ₃ Ni ₂	hP5	<i>Pm</i> 31	Al ₃ Ni ₂	0.918		
η	In ₇₂ Ni ₂₈			γ brass			
(a) Numbers in parent	theses are in at.% In						

Table 1 Phases in the Ge-In, Ge-Ni, and In-Ni binary systems and their structure data

quenched. Only x-ray diffraction (XRD) was used for phase identification and phase boundary determination. For XRD work the alloys were powdered, sealed in evacuated quartz tubes, recrystallized at 650 °C, and then quenched in water. The 650 °C isothermal section established by [1982Bor] is given in Fig. 4 after making some adjustments of phase boundaries to agree with the accepted binary data.

To determine the 650 °C isothermal section [1982Bor] used only a few alloys containing from about 25 at.% Ge and In to about 65 at.% Ge and In, and hence only a partial isothermal section was established. The fcc γ phase boundary at the Ni corner was not experimentally determined, and the γ phase boundary does not agree with the binary In-Ni and Ge-Ni systems. The probable γ phase boundary is shown schematically in Fig. 4. The binary phases τ , β , λ , ρ , ν , and ι phases were found to extend into the ternary only marginally, <2 at.% In or Ge. The τ and β phases were found in equilibrium with each other and are found in equilibrium with the ε phase. A three-phase region $\gamma + \tau + \beta$ should exist and is shown schematically in Fig. 4. The isostructural Ge₃Ni₅ and In₉Ni₁₆ phases form a continuous solid solution region ε extending from the Ge-Ni binary to the In-Ni binary. [1982Bor], however, had shown the ε phase region to extend up to ~41 at.% Ge at the Ge-Ni binary, which does not agree with the accepted binary data. The Ge-Ni binary indicates at 650 °C the solubility of Ge in the ε phase to be about 38 at.% Ge, and between 38 and 41 at.% Ge two more intermediate phases ζ and ξ exist in the Ge-Ni binary. [1982Bor] did not show these two phases. [1982Bor] also found a phase Ni₃In₇ extending from the In-Ni binary up to ~15 at.% Ge. The accepted In-Ni binary does not have an In7Ni3 phase, but has an In72Ni28 phase that exists at temperature <409 °C. The In₇Ni₃ phase is possibly the $In_{72}Ni_{28}$ phase (η). This probably means that the low-temperature phase In₇₂Ni₂₈ phase is stabilized to higher temperature by the addition of Ge. The η phase in the ternary thus cannot extend to the In-Ni binary at 650 °C. Accordingly, the n phase boundary has been terminated close to the In-Ni binary and an expected three-phase equilibrium triangle $L + \eta + v$ has been shown schematically in Fig. 4. At 650 °C a liquid region (L) should exist at the In corner of the Ge-In-Ni system and phase equilibrium involving the L and η and Ge should exist. This was not shown by [1982Bor], and in Fig. 4 a three-phase equilibrium triangle $L + \eta + Ge$ is shown schematically by dashed lines. The ε , v, and θ phases were found in equilibrium. Phase equilibrium involving the λ and ρ phases was not determined by [1982Bor]. The probable three-phase equilibrium $\varepsilon + \tau + \tau$ λ and $\varepsilon + \rho + \theta$ are shown schematically in Fig. 4. At the high Ge side of the Ge-In-Ni system the n phase was found in equilibrium with the 1 phase and Ge. [1982Bor] reported that the η phase is in equilibrium with the ι and ε phases. Since [1982Bor] did not find the ζ and ξ phases in their study of the Ge-In-Ni phase diagram, it may be assumed that the ζ and ξ phases do not extend far into the ternary. As a result of the shift of the high Ge side of the ε phase boundary (Fig. 4)



Fig. 4 An isothermal section of the Ge-In-Ni system at 650 °C [1982Bor]

and the possible presence of the ζ and ξ phases, the boundaries of the three-phase region $\varepsilon + \iota + \eta$ had to be shifted slightly (shown schematically by dashed lines) from that given by [1982Bor]. Because of these small adjustments made in the 650 °C isothermal section of the Ge-In-Ni system, and because the phase boundaries given in Fig. 1 are sometimes based on only one or two alloys using XRD only, it will be necessary to determine proper phase boundaries using various other techniques.

References

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1991Nas: P. Nash, *Phase Diagrams of Binary Nickel Alloys*, ASM International, Metals Park, OH, 1991 (Review)

indicates presence of phase diagram.

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